

Product specifications

Case	T039
Type	Transistor Silicon NPN
Manufacturer	Texas Instruments
Vbr CBO	185
Vbr CEO	180
Max. PD (W)	1.0
Max. hFE	60
Min hFE	20
Ic Max. (A)	100m
@Ic (test) (A)	30m
Icbo Max. @Vcb Max. (A)	100u+
Polarity	NPN
Derate Above 25°C	40m
Trans. Freq (Hz) Min.	80M
Oper. Temp (°C) Max.	175
@VCE (V)	10
Pinout Equivalence Number	3-12
Surface Mounted Yes/No	NO
Maximum Collector Power Dissipation (Pc)	0.8 W
Maximum Collector-Base Voltage Vcb	185 V
Maximum Collector-Emitter Voltage Vce	180 V
Maximum Emitter-Base Voltage Veb	5 V
Maximum Collector Current Ic max	0.1 A
Max. Operating Junction Temperature (Tj)	200 °C
Collector Capacitance (Cc)	6 pF
Transition Frequency (ft):	80 MHz
Forward Current Transfer Ratio (hFE), MIN	20
SKU	86332